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providing a semiconductor structure having [the] a base layer, [the] an insulation layer, and [the] a monocrystalline silicon layer;

introducing [the] a passivating substance X [into one of] between the insulation layer and the monocrystalline silicon layer [during or after the fabrication of the semiconductor structure]; and

*B*  
heat-treating the semiconductor structure with the passivating substance X, thereby, causing the passivating substance to diffuse into an interface between the insulation layer and the monocrystalline silicon layer.

*WJ*

Claim 12 (amended). The method according to claim 7, which comprises patterning the monocrystalline silicon layer by etching away regions thereof down to [the] an underlying insulation layer.

Remarks:

Reconsideration of the application is requested.

Claims 1-15 are remain in the application. Claims 7 and 12 have been amended. Claims 1-6 have been withdrawn from consideration.